

AMENDMENTS TO THE CLAIMS:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-6 are cancelled.

7. (New) An SOI wafer in which at least a silicon active layer is formed on a support substrate, wherein at least the silicon active layer consists of silicon single crystal grown by Chochralski method, which is occupied by N region outside OSF generated in a shape of a ring and has no defect region detected by Cu deposition method.
8. (New) The SOI wafer according to Claim 7, wherein a thickness of the silicon active layer is 200 nm or less.
9. (New) The SOI wafer according to claim 7, wherein the silicon active layer is formed by being bonded to the support substrate via an oxide film.
10. (New) The SOI wafer according to claim 8, wherein the silicon active layer is formed by being bonded to the support substrate via an oxide film.
11. (New) The SOI wafer according to claim 9, wherein a thickness of the oxide film is in the range from 2 nm to 3000 nm.
12. (New) The SOI wafer according to claim 10, wherein a thickness of the oxide film is in the range from 2 nm to 3000 nm.

13. (New) The SOI wafer according to claim 7, wherein the SOI wafer is produced by ion implantation delamination method.
14. (New) The SOI wafer according to claim 8, wherein the SOI wafer is produced by ion implantation delamination method.
15. (New) The SOI wafer according to claim 9, wherein the SOI wafer is produced by ion implantation delamination method.
16. (New) The SOI wafer according to claim 10, wherein the SOI wafer is produced by ion implantation delamination method.
17. (New) The SOI wafer according to claim 11, wherein the SOI wafer is produced by ion implantation delamination method.
18. (New) The SOI wafer according to claim 12, wherein the SOI wafer is produced by ion implantation delamination method.
19. (New) A method for producing an SOI wafer comprising steps of, in a bond wafer that is to be a silicon active layer and a base wafer that is to be a support substrate, implanting hydrogen ions, rare gas ions or mixture gas ions of these gases from a surface of the bond wafer to form an ion-implanted layer inside the bond wafer, bonding the surface of the ion-implanted side of the bond wafer and a surface of the base wafer via an oxide film or directly, and delaminating a part of the bond wafer at the ion-implanted layer by heat treatment to form an SOI wafer, wherein a silicon wafer consisting of silicon single crystal grown by

Chochralski method, which is occupied by N region outside OSF generated in a shape of a ring and has no defect region detected by Cu deposition method, is used as the bond wafer.